

STANDARD RECOVERY DIODES

Stud Version

Features

- Wide current range
- High voltage ratings up to 2400V
- High surge current capabilities
- Stud cathode and stud anode version
- Standard JEDEC types
- RoHS Compliant

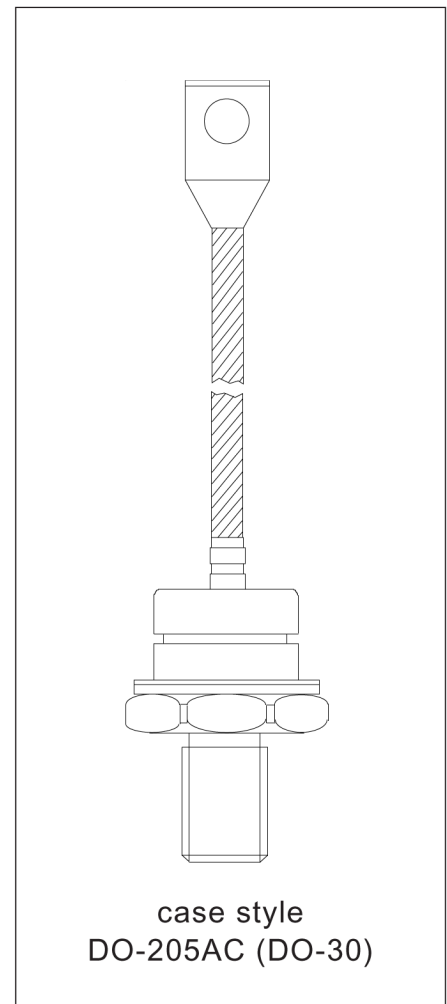
200A

Typical Applications

- Converters
- Power supplies
- Machine tool controls
- High power drives
- Medium traction applications

Major Ratings and Characteristics

Parameters	SD200N/R		Units
	1600 to 2000	2400	
$I_{F(AV)}$	200	200	A
@ T_C	110	110	°C
$I_{F(RMS)}$	314	314	A
I_{FSM}			
@ 50Hz	4700	4700	A
@ 60Hz	4920	4920	A
I^2t			
@ 50Hz	110	110	KA ² s
@ 60Hz	101	101	KA ² s
V_{RRM} range	1600 to 2000	2400	V
T_J	- 40 to 180	150	°C



ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{RRM} , maximum repetitive peak reverse voltage V	V_{RSM} , maximum non-repetitive peak rev. voltage V	I_{RRM} max. @ $T_J = T_J$ max. mA
SD200N/R	16	1600	1700	15
	20	2000	2100	
	24	2400	2500	

Forward Conduction

Parameter	SD200N/R	Units	Conditions
$I_{F(AV)}$ Max. average forward current @ Case temperature	200	A	180° conduction, half sine wave
	110	°C	
$I_{F(AV)}$ Max. average forward current @ Case temperature	220	A	180° conduction, half sine wave
	100	°C	
$I_{F(RMS)}$ Max. RMS forward current	314	A	DC @ 95°C case temperature
I_{FSM} Max. peak, one-cycle forward, non-repetitive surge current	4700	A	t = 10ms No voltage
	4920		t = 8.3ms reapplied
	3950		t = 10ms 100% V_{RRM}
	4140		t = 8.3ms reapplied
I^2t Maximum I^2t for fusing	110	KA ² s	t = 10ms No voltage
	101		t = 8.3ms reapplied
	78		t = 10ms 100% V_{RRM}
	71		t = 8.3ms reapplied
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	1100	KA ² √s	t = 0.1 to 10ms, no voltage reapplied
$V_{F(TO)1}$ Low level value of threshold voltage	0.90	V	(16.7% $\times \pi \times I_{F(AV)} < I < \pi \times I_{F(AV)}$), $T_J = T_J$ max.
$V_{F(TO)2}$ High level value of threshold voltage	1.00		($I > \pi \times I_{F(AV)}$), $T_J = T_J$ max.
r_{f1} Low level value of forward slope resistance	0.79	mΩ	(16.7% $\times \pi \times I_{F(AV)} < I < \pi \times I_{F(AV)}$), $T_J = T_J$ max.
r_{f2} High level value of forward slope resistance	0.64		($I > \pi \times I_{F(AV)}$), $T_J = T_J$ max.
V_{FM} Max. forward voltage drop	1.40	V	$I_{pk} = 630A$, $T_J = T_J$ max, $t_p = 10ms$ sinusoidal wave

Thermal and Mechanical Specifications

Parameter	SD200N/R		Units	Conditions
	1600 to 2000	2400		
T _J Max. junction operating temperature range	-40 to 180	-40 to 150	°C	
T _{stg} Max. storage temperature range	-55 to 200			
R _{thJC} Max. thermal resistance, junction to case	0.23		K/W	DC operation
R _{thCS} Max. thermal resistance, case to heatsink	0.08			Mounting surface, smooth, flat and greased
T Max. allowed mounting torque ±10%	14		Nm	Not lubricated threads
wt Approximate weight	120		g	
Case style	DO-205AC(DO-30)		See Outline Table	

ΔR_{thJC} Conduction

(The following table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction	Rectangular conduction	Units	Conditions
180°	0.041	0.030	K/W	T _J = T _J max.
120°	0.049	0.051		
90°	0.063	0.068		
60°	0.093	0.096		
30°	0.156	0.157		

Ordering Information Table

Device Code

SD	20	0	N	24	P	C
①	②	③	④	⑤	⑥	⑦

- 1** - Diode
- 2** - Essential part number
- 3** - 0 = Standard recovery
- 4** - N = Stud Normal Polarity (Cathode to Stud)
R = Stud Reverse Polarity (Anode to Stud)
- 5** - Voltage code: Code x 100 = V_{RRM} (See Voltage Ratings table)
- 6** - P = Stud base DO-205AC (DO-30) 1/2" 20UNF-2A
M = Stud base DO-205AC (DO-30) M12 X 1.75
- 7** - C = Ceramic Housing

For Metric Device M12 x 1.75 Contact Factory

Outline Table

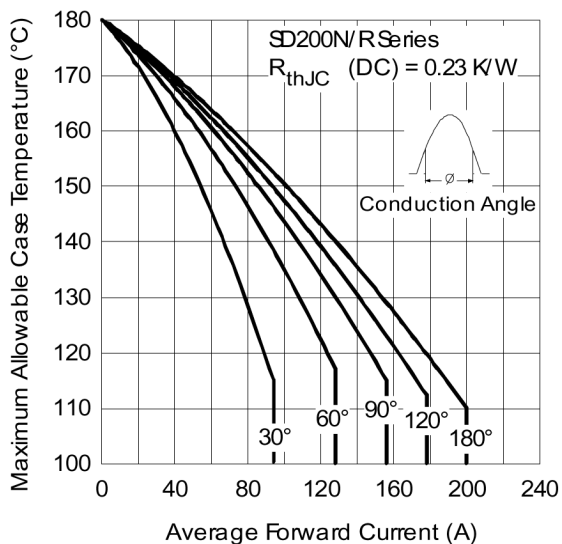
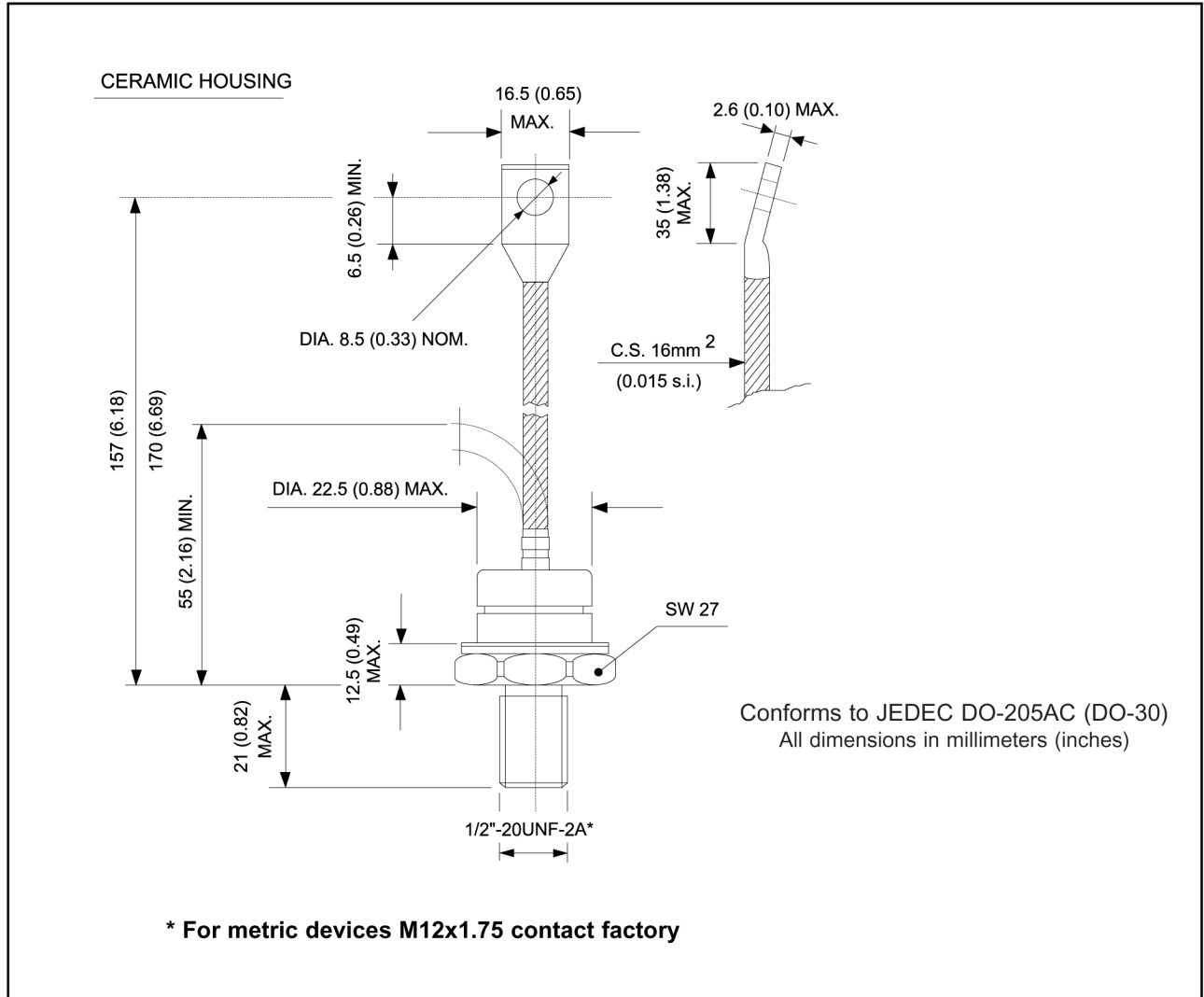


Fig. 1 - Current Ratings Characteristics

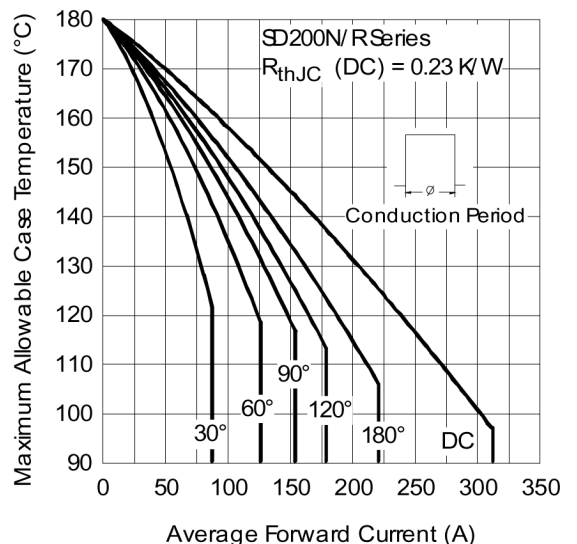


Fig. 2 - Current Ratings Characteristics